

2811

O I P E
SEP 17 2001

Please type a plus sign (+) inside this box →

Approved for use through 10/31/02. OMB 0651-0031
 U.S. Patent and Trademark Office; U.S. DEPARTMENT OF COMMERCE

Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it displays a valid OMB control number.

TRANSMITTAL FORM

(to be used for all correspondence after initial filing)

Total Number Of Pages In This Submission

8

Application Number

09/557,961

Filing Date

April 25, 2001

First Named Inventor

Kunihiro TAKATANI

Group Art Unit

2811

Examiner Name

Donghee Kang

TECHNOLOGY REC'D

REC'D 20

20

20

20

Attorney Docket No. 245402001600

ENCLOSURES (check all that apply)

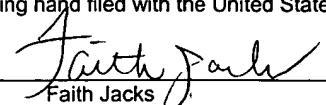
<input type="checkbox"/> Fee Transmittal Form	<input type="checkbox"/> Assignment Papers (for an Application)	<input type="checkbox"/> After Allowance Communication to Group
<input type="checkbox"/> Fee Attached	<input type="checkbox"/> Drawing(s)	<input type="checkbox"/> Appeal Communication to Board of Appeals and Interferences
<input checked="" type="checkbox"/> Amendment / Reply	<input type="checkbox"/> Licensing-related Papers	<input type="checkbox"/> Appeal Communication to Group (Appeal Notice, Brief, Reply Brief)
<input type="checkbox"/> After Final	<input type="checkbox"/> Petition	<input type="checkbox"/> Proprietary Information
<input type="checkbox"/> Affidavits/declarations	<input type="checkbox"/> Petition to Convert to a Provisional Application	<input type="checkbox"/> Status Letter
<input type="checkbox"/> Extension of Time Request	<input type="checkbox"/> Power of Attorney, Revocation Change of Correspondence Address	<input type="checkbox"/> Other Enclosure(s) (please identify below):
<input type="checkbox"/> Express Abandonment Request	<input type="checkbox"/> Terminal Disclaimer	
<input type="checkbox"/> Information Disclosure Statement	<input type="checkbox"/> Request for Refund	
<input type="checkbox"/> Certified Copy of Priority Document(s)	<input type="checkbox"/> CD, Number of CD(s) _____	
<input type="checkbox"/> Response to Missing Parts/ Incomplete Application	<input type="checkbox"/> Remarks	
<input type="checkbox"/> Response to Missing Parts under 37 CFR 1.52 or 1.53		

SIGNATURE OF APPLICANT, ATTORNEY OR AGENT

Firm or Individual Name	Jonathan Bockman Registration No. 45,640 Morrison & Foerster LLP 2000 Pennsylvania Avenue, N.W. Washington, D.C. 20006-1888 (202) 778-1601
Signature	
Date	September 17, 2001

CERTIFICATE OF HAND DELIVERY

I hereby certify that this correspondence is being hand filed with the United States Patent and Trademark Office in Washington, D.C. on September 17, 2001.


Faith Jacks

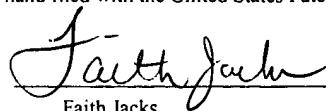
Burden Hours Statement: This form is estimated to take 0.2 hours to complete. Time will vary depending upon the needs of the individual case. Any comments on the amount of time you are required to complete this form should be sent to the Chief Information Officer, U.S. Patent and Trademark Office, Washington, DC 20231. DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS. SEND TO: Assistant Commissioner for Patents, Box Patent Application, Washington, DC 20231.



PATENT
Docket No. 245402001600

CERTIFICATE OF HAND DELIVERY

I hereby certify that this correspondence is being hand filed with the United States Patent and Trademark Office in Washington, D.C. on September 17, 2001.


Faith Jacks

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In the application of:

Kunihiro TAKATANI

Serial No.: 09/557,961

Filing Date: April 25, 2000

For: ELECTRODE STRUCTURE ON P-TYPE III GROUP NITRIDE SEMICONDUCTOR LAYER AND FORMATION METHOD THEREOF

Examiner: Donghee Kang

Group Art Unit: 2811

RECEIVED
SEP 20 2001
TECHNOLOGY CENTER 2800

#9/AUOT
A
9/25/01
V/S

AMENDMENT UNDER 37 CFR 1.111

Commissioner for Patents
Washington, D.C. 20231

Sir:

In response to the Office Action dated June 15, 2001, please amend this application as follows:

AMENDMENTS

In the Claims:

Subt B Please amend claim 1 as follows:

C 1. (Amended) An electrode structure on a p-type III group nitride semiconductor layer, comprising first, second and third electrode layers successively stacked on said semiconductor layer,